

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Rathi et al.

Serial No.: 09/165,248

Confirmation No.: 7619

Filed: October 1, 1998

For: A SILICON CARBIDE
DEPOSITION AS A BARRIER
LAYER AND AN ETCH STOP



Group Art Unit: 2811

Examiner: G. Fourson

TECHNOLOGY CENTER 2800

AUG 30 2001

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Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

CERTIFICATE OF MAILING 37 CFR 1.8	
I hereby certify that this correspondence is being deposited on August 24, 2001, with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.	
8/24/01 Date	<i>[Signature]</i> Signature

RESPONSE TO OFFICE ACTION DATED APRIL 25, 2001

In response to the Office Action dated April 25, 2001, having a shortened statutory period for response extended one month to expire on August 25, 2001, please enter the following amendments and reconsider the claims pending in the application for reasons discussed below.

IN THE CLAIMS:

Please cancel claims 9 and 14 without prejudice, and amend the following claims:

- (Amended) A method for processing a substrate, comprising:
depositing a silicon carbide barrier layer on the substrate by a method comprising:
introducing an alkylsilane and a noble gas into a chamber;
initiating a plasma in the chamber;